

[Designation of Document] Abstract

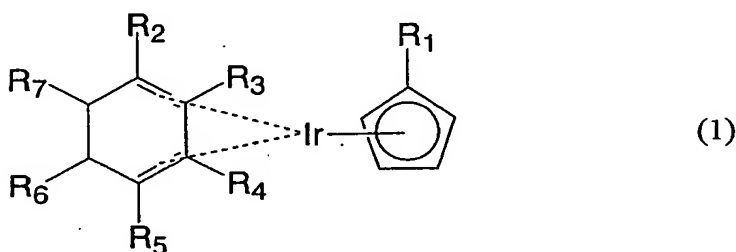
[Abstract]

[Problems]

To provide an organometallic compound for forming a thin film comprising iridium or iridium oxide on a substrate by CVD process, the compound having a low melting point, excellent vaporization characteristic and low film formation temperature on the substrate.

[Means for Resolution]

An organometallic iridium compound represented by the following general formula (1):



wherein R<sub>1</sub>, R<sub>2</sub>, R<sub>3</sub>, R<sub>4</sub>, R<sub>5</sub>, R<sub>6</sub>, and R<sub>7</sub> are the same or different and each represents hydrogen, a halogen, a lower acyl group, a lower alkoxy group, a lower alkoxycarbonyl group, or a lower alkyl group, provided that the case where all of R<sub>1</sub>, R<sub>2</sub>, R<sub>3</sub>, R<sub>4</sub>, R<sub>5</sub>, R<sub>6</sub>, and R<sub>7</sub> represent hydrogen is excluded (representative compound: (ethylcyclopentadienyl)(1,3-cyclohexadiene)iridium).

[Selected Drawing] Fig. 1